

Abstract  
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The invention concerns a method of making a complex microelectronic structure by assembling two substrates through two respective linking surfaces, the structure being designed to be dissociated at a separation zone. The invention is characterized in that it consists, prior to assembly, in producing a state difference in the tangential stresses between the two surfaces to be assembled, said difference being selected so as to obtain in the assembled structure a predetermined stress state at the time of dissociation.